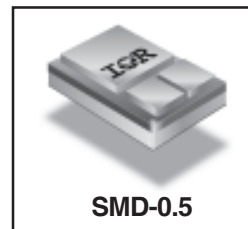


**RADIATION HARDENED
 POWER MOSFET
 SURFACE-MOUNT (SMD-0.5)**

**2N7598U3
 IRHNJ67C30
 600V, N-CHANNEL
 R₆ TECHNOLOGY**

Product Summary

Part Number	Radiation Level	R _{DS(on)}	I _D
IRHNJ67C30	100K Rads (Si)	2.9Ω	3.4A
IRHNJ63C30	300K Rads (Si)	2.9Ω	3.4A



International Rectifier's R6™ technology provides superior power MOSFETs for space applications. These devices have improved immunity to Single Event Effect (SEE) and have been characterized for useful performance with Linear Energy Transfer (LET) up to 90MeV/(mg/cm²).

Their combination of very low R_{DS(on)} and faster switching times reduces power loss and increases power density in today's high speed switching applications such as DC-DC converters and motor controllers. These devices retain all of the well established advantages of MOSFETs such as voltage control, ease of paralleling and temperature stability of electrical parameters.

Features:

- Low R_{DS(on)}
- Fast Switching
- Single Event Effect (SEE) Hardened
- Low Total Gate Charge
- Simple Drive Requirements
- Ease of Paralleling
- Hermetically Sealed
- Surface Mount
- Ceramic Package
- Light Weight

Absolute Maximum Ratings

Pre-Irradiation

	Parameter		Units
I _D @ V _{GS} = 12V, T _C = 25°C	Continuous Drain Current	3.4	A
I _D @ V _{GS} = 12V, T _C = 100°C	Continuous Drain Current	2.2	
I _{DM}	Pulsed Drain Current ①	13.6	
P _D @ T _C = 25°C	Max. Power Dissipation	75	W
	Linear Derating Factor	0.6	W/°C
V _{GS}	Gate-to-Source Voltage	±20	V
EAS	Single Pulse Avalanche Energy ②	76	mJ
I _{AR}	Avalanche Current ①	3.4	A
EAR	Repetitive Avalanche Energy ①	7.5	mJ
dv/dt	Peak Diode Recovery dv/dt ③	9.2	V/ns
T _J	Operating Junction	-55 to 150	°C
T _{STG}	Storage Temperature Range		
	Pckg. Mounting Surface Temp.	300 (for 5s)	
	Weight	1.0 (Typical)	g

For footnotes refer to the last page

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Electrical Characteristics @ T_j = 25°C (Unless Otherwise Specified)

	Parameter	Min	Typ	Max	Units	Test Conditions
BV _{DSS}	Drain-to-Source Breakdown Voltage	600	—	—	V	V _{GS} = 0V, I _D = 1.0mA
ΔBV _{DSS} /ΔT _J	Temperature Coefficient of Breakdown Voltage	—	0.47	—	V/°C	Reference to 25°C, I _D = 1.0mA
R _{DS(on)}	Static Drain-to-Source On-State Resistance	—	—	2.9	Ω	V _{GS} = 12V, I _D = 2.2A ④
V _{GS(th)}	Gate Threshold Voltage	2.0	—	4.0	V	V _{DS} = V _{GS} , I _D = 1.0mA
g _{fs}	Forward Transconductance	3.4	—	—	S	V _{DS} = 15V, I _{DS} = 2.2A ④
I _{DSS}	Zero Gate Voltage Drain Current	—	—	10	μA	V _{DS} = 480V, V _{GS} = 0V
		—	—	25		V _{DS} = 480V, V _{GS} = 0V, T _J = 125°C
I _{GSS}	Gate-to-Source Leakage Forward	—	—	100	nA	V _{GS} = 20V
I _{GSS}	Gate-to-Source Leakage Reverse	—	—	-100		V _{GS} = -20V
Q _g	Total Gate Charge	—	—	35	nC	V _{GS} = 12V, I _D = 3.4A V _{DS} = 300V
Q _{gs}	Gate-to-Source Charge	—	—	12		
Q _{gd}	Gate-to-Drain ('Miller') Charge	—	—	15		
t _{d(on)}	Turn-On Delay Time	—	—	17	ns	V _{DD} = 300V, I _D = 3.4A, V _{GS} = 12V, R _G = 7.5Ω
t _r	Rise Time	—	—	9.3		
t _{d(off)}	Turn-Off Delay Time	—	—	33		
t _f	Fall Time	—	—	17		
L _S + L _D	Total Inductance	—	4.0	—	nH	Measured from the center of drain pad to center of source pad
C _{iss}	Input Capacitance	—	1222	—	pF	V _{GS} = 0V, V _{DS} = 25V f = 1.0MHz
C _{oss}	Output Capacitance	—	80	—		
C _{rss}	Reverse Transfer Capacitance	—	1.9	—		
R _g	Internal Gate Resistance	—	1.5	—		

Source-Drain Diode Ratings and Characteristics

	Parameter	Min	Typ	Max	Units	Test Conditions
I _S	Continuous Source Current (Body Diode)	—	—	3.4	A	T _j = 25°C, I _S = 3.4A, V _{GS} = 0V ④
I _{SM}	Pulse Source Current (Body Diode) ①	—	—	13.6		
V _{SD}	Diode Forward Voltage	—	—	1.0	V	T _j = 25°C, I _F = 3.4A, di/dt ≤ 100A/μs
t _{rr}	Reverse Recovery Time	—	—	741	ns	V _{DD} ≤ 50V ④
Q _{RR}	Reverse Recovery Charge	—	—	2.1	μC	
t _{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible. Turn-on speed is substantially controlled by L _S + L _D .				

Thermal Resistance

	Parameter	Min	Typ	Max	Units	Test Conditions
R _{thJC}	Junction-to-Case	—	—	1.67	°C/W	

Note: Corresponding Spice and Saber models are available on International Rectifier Web site.

For footnotes refer to the last page

Radiation Characteristics

IRHNJ67C30, 2N7598U3

International Rectifier Radiation Hardened MOSFETs are tested to verify their radiation hardness capability. The hardness assurance program at International Rectifier is comprised of two radiation environments. Every manufacturing lot is tested for total ionizing dose (per notes 5 and 6) using the TO-3 package. Both pre- and post-irradiation performance are tested and specified using the same drive circuitry and test conditions in order to provide a direct comparison.

Table 1. Electrical Characteristics @ T_j = 25°C, Post Total Dose Irradiation ⑤⑥

	Parameter	Up to 300K Rads (Si) ¹		Units	Test Conditions
		Min	Max		
BV _{DSS}	Drain-to-Source Breakdown Voltage	600	—	V	V _{GS} = 0V, I _D = 1.0mA
V _{GS(th)}	Gate Threshold Voltage	2.0	4.0		V _{GS} = V _{DS} , I _D = 1.0mA
I _{GSS}	Gate-to-Source Leakage Forward	—	100	nA	V _{GS} = 20V
I _{GSS}	Gate-to-Source Leakage Reverse	—	-100		V _{GS} = -20V
I _{DSS}	Zero Gate Voltage Drain Current	—	10	μA	V _{DS} = 480V, V _{GS} = 0V
R _{DS(on)}	Static Drain-to-Source On-State Resistance (TO-3) ④	—	2.9	Ω	V _{GS} = 12V, I _D = 2.2A
V _{SD}	Diode Forward Voltage ④	—	1.0	V	V _{GS} = 0V, I _D = 3.4A

1. Part numbers IRHNJ67C30 and IRHNJ63C30

International Rectifier radiation hardened MOSFETs have been characterized in heavy ion environment for Single Event Effects (SEE). Single Event Effects characterization is illustrated in Fig. a and Table 2.

Table 2. Single Event Effect Safe Operating Area

Ion	LET (MeV/(mg/cm ²))	Energy (MeV)	Range (μm)	V _{DS} (V)			
				@V _{GS} = 0V	@V _{GS} = -4V	@V _{GS} = -12V	@V _{GS} = -20V
Kr	32.4	679	83.3	600	600	600	600
Xe	56.2	1060	83.5	600	600	600	-
Au	89.5	1555	84	600	600	-	-

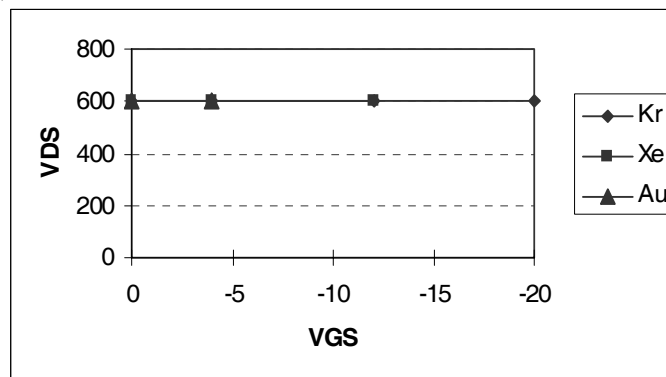
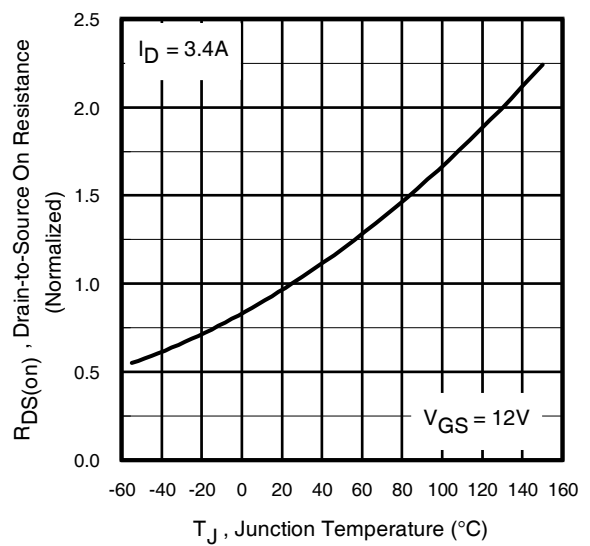
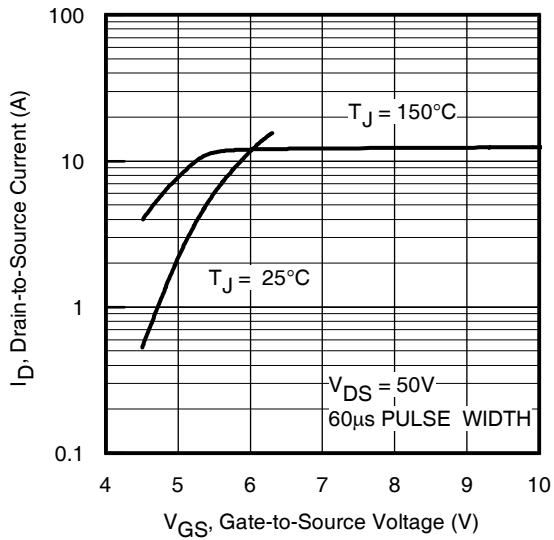
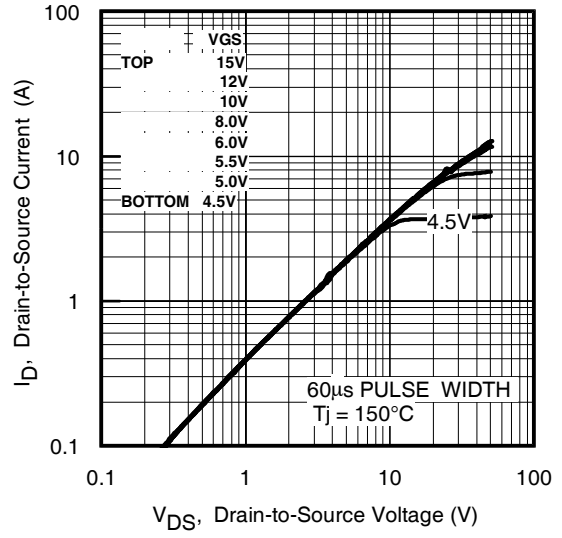
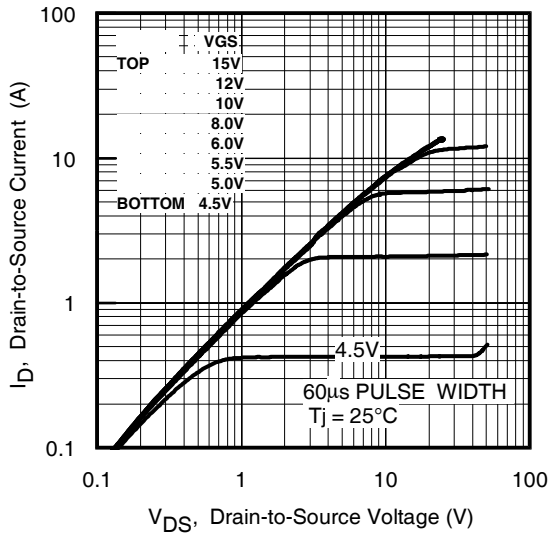


Fig a. Single Event Effect, Safe Operating Area

For footnotes refer to the last page



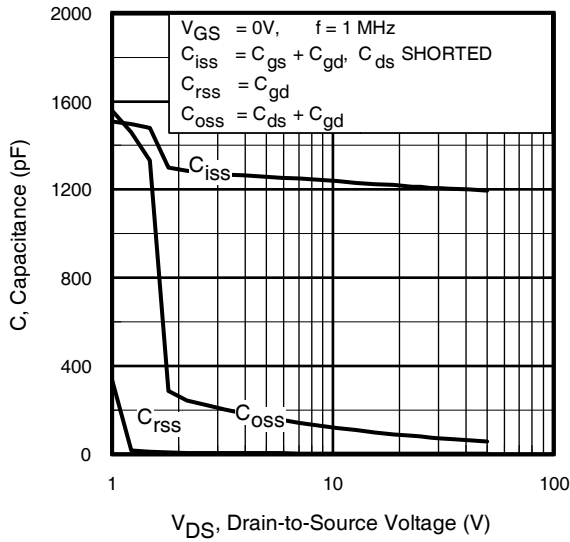


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

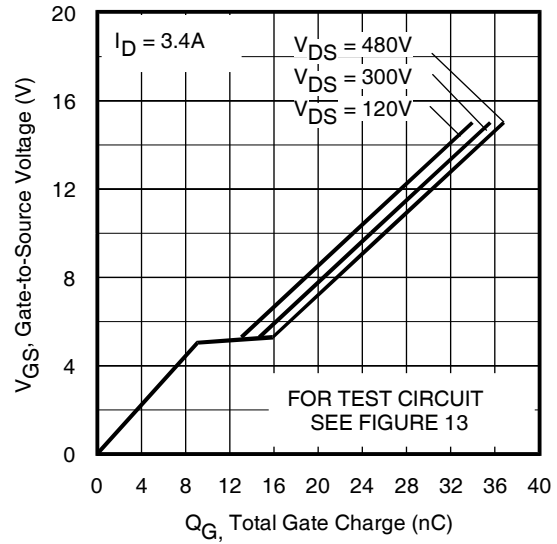


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

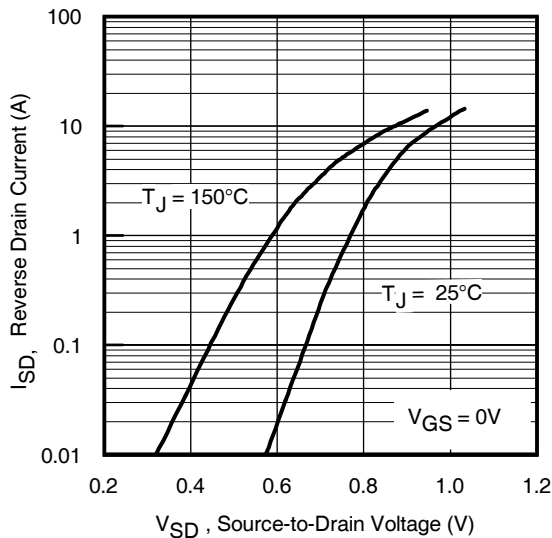


Fig 7. Typical Source-Drain Diode Forward Voltage

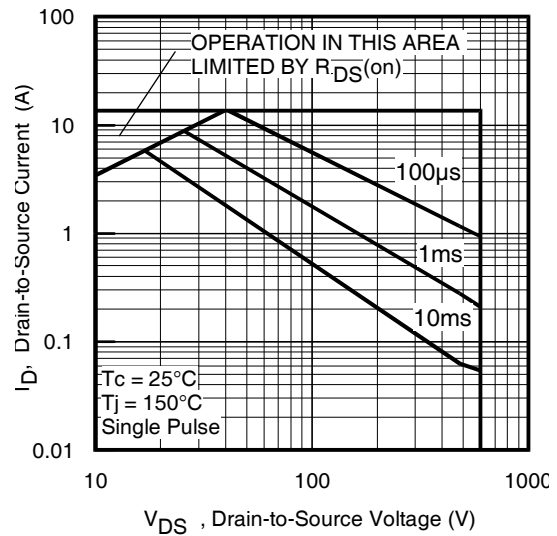


Fig 8. Maximum Safe Operating Area

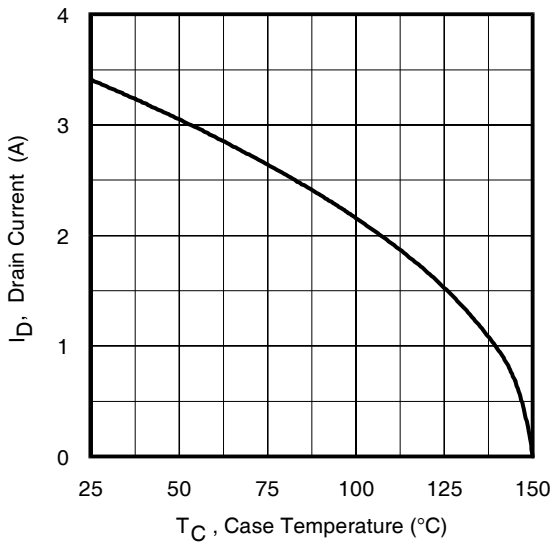


Fig 9. Maximum Drain Current Vs. Case Temperature

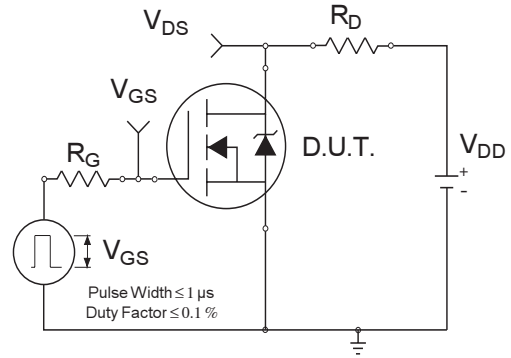


Fig 10a. Switching Time Test Circuit

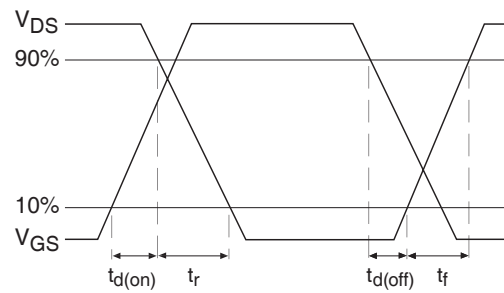


Fig 10b. Switching Time Waveforms

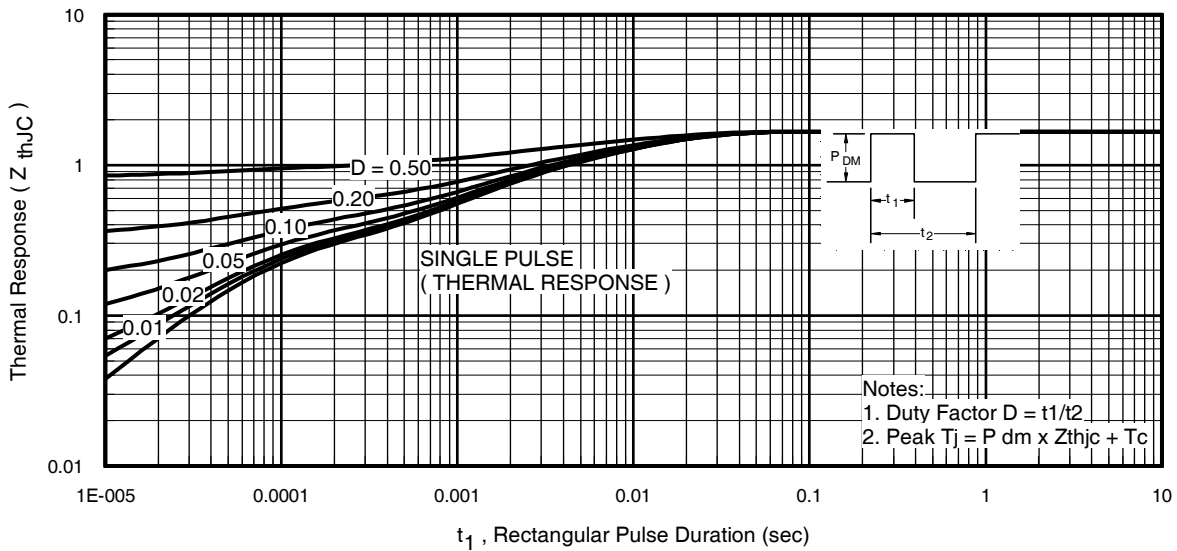


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

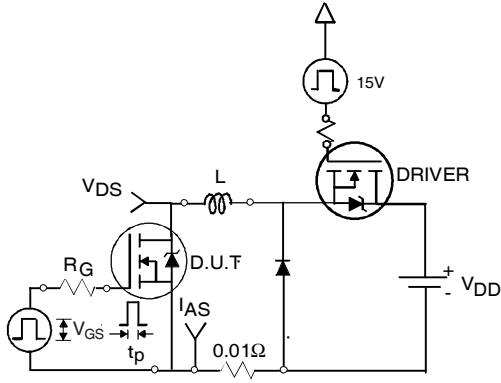


Fig 12a. Unclamped Inductive Test Circuit

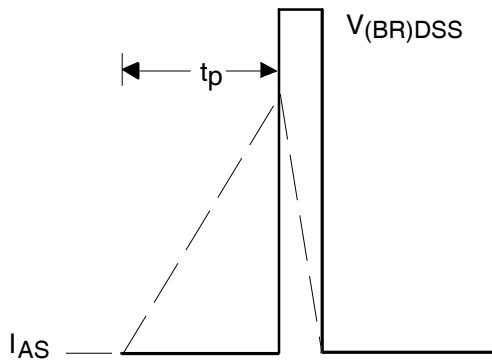


Fig 12b. Unclamped Inductive Waveforms

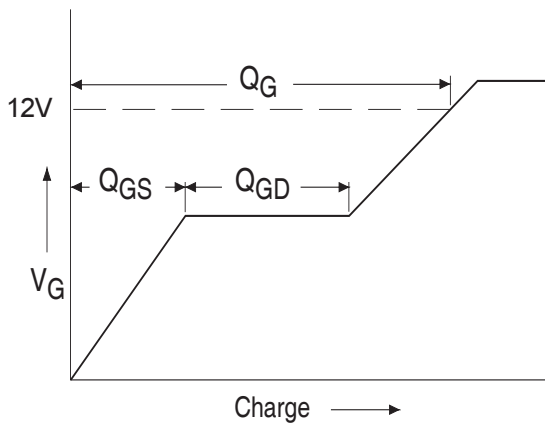


Fig 13a. Basic Gate Charge Waveform

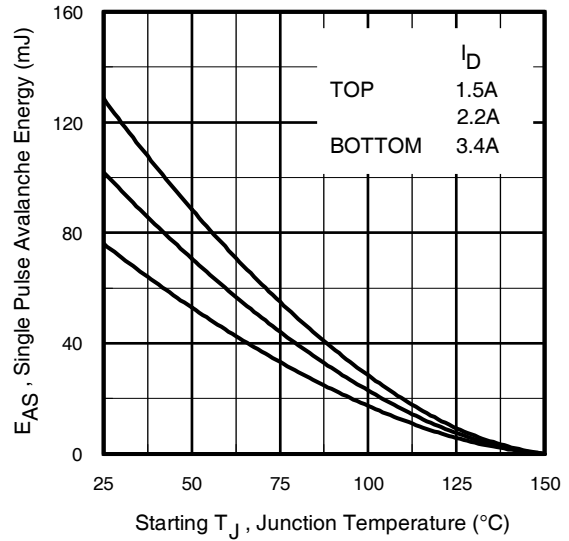


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

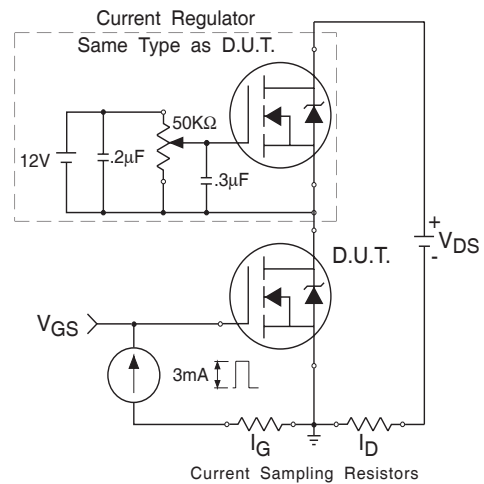
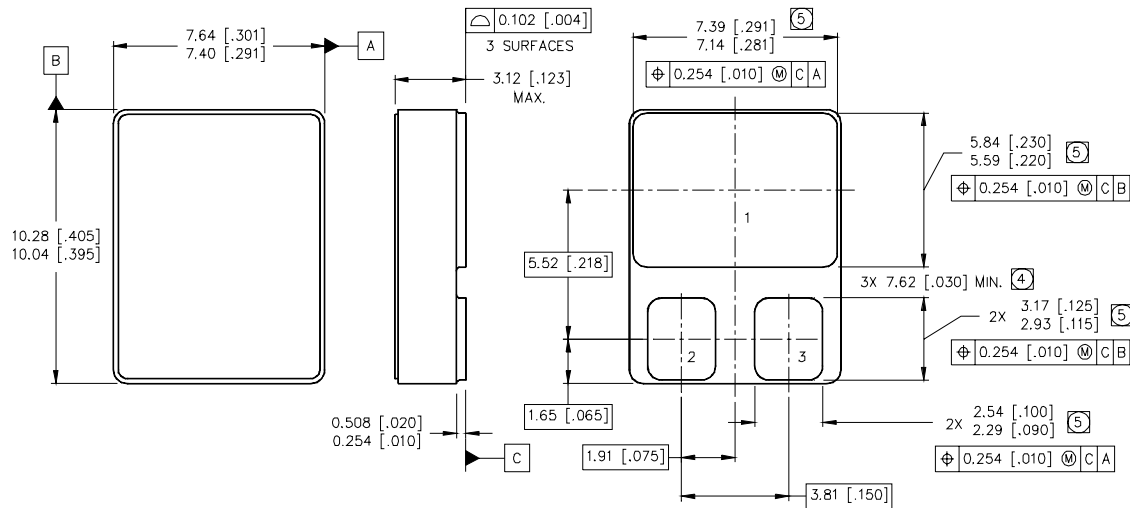


Fig 13b. Gate Charge Test Circuit

Footnotes:

- ① Repetitive Rating; Pulse width limited by maximum junction temperature.
- ② $V_{DD} = 50V$, starting $T_J = 25^\circ C$, $L = 13mH$
Peak $I_L = 3.4A$, $V_{GS} = 12V$
- ③ $I_{SD} \leq 3.4A$, $di/dt \leq 628A/\mu s$,
 $V_{DD} \leq 600V$, $T_J \leq 150^\circ C$
- ④ Pulse width $\leq 300 \mu s$; Duty Cycle $\leq 2\%$
- ⑤ **Total Dose Irradiation with V_{GS} Bias.**
12 volt V_{GS} applied and $V_{DS} = 0$ during irradiation per MIL-STD-750, method 1019, condition A.
- ⑥ **Total Dose Irradiation with V_{DS} Bias.**
480 volt V_{DS} applied and $V_{GS} = 0$ during irradiation per MIL-STD-750, method 1019, condition A.

Case Outline and Dimensions — SMD-0.5



NOTES:

- 1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
- 2. CONTROLLING DIMENSION: INCH.
- 3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
- ④ DIMENSION INCLUDES METALLIZATION FLASH.
- ⑤ DIMENSION DOES NOT INCLUDE METALLIZATION FLASH.

PAD ASSIGNMENTS

- 1 = DRAIN
- 2 = GATE
- 3 = SOURCE

International
IR Rectifier

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